

SBR20150CT SBR20150CTF SBR20150CTI SBR20150CTB

Super Barrier Rectifier ™

Using state-of-the-art SBR IC process technology, the following features are made possible in a single device:

Major ratings and characteristics

Characteristics	Values	Units
I _{F(AV)} Rectangular Waveform	20	Α
V_{RRM}	150	V
V _F @10A, Tj=125 ^O C	0.71	V, typ
Tj (operating/storage)	-65 to 175	°C

ELECTRICAL:

- * Low Forward Voltage Drop
- * Reliable High Temperature Operation
- * Super Barrier Design
- * Softest, Fast Switching Capability
- * 175°C Operating Junction Temperature

Device optimized for high temperature Power Supply applications

MECHANICAL:

* Molded Plastic TO-220AB, TO-262, TO-263, and ITO-220 packages

Case Styles						
SBR20150CT	SBR20150CTF	SBR20150CTI	SBR20150CTB			
Confinon Cathode Allode	Anode 1 Cathode 3 Anode	2 Common 3 Anode	2 Common Cathode Anode			
TO-220AB	ITO-220	TO-262	TO-263			



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	SYMBOL			UNITS
DC Blocking Voltage Working Peak Reverse Voltage Peak Repetitive Reverse Voltage	V _{RM} V _{RWM} V _{RRM}	150		Volts
Average Rectified Forward Current (Rated V _R -20Khz Square Wave) - 50% duty cycle	Io	20		Amps
Peak Forward Surge Current - 1/2 60hz	I _{FSM}	120		Amps
Peak Repetitive Reverse Surge Current (2uS-1Khz)	I _{RRM}	2		Amps
Instantaneous Forward Voltage (per leg) $I_F = 10A$; $T_J = 25^{\circ}C$ $I_F = 10A$; $T_J = 125^{\circ}C$	V _F	Тур 	Max 0.88 0.79	Volts
Maximum Instantaneous Reverse Current at Rated V_{RM} $T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$	I _R *	Тур 	Max 100 10	uA mA
Maximum Rate of Voltage Change (at Rated V_R)	d∨/dt	10,000		V/uS
Maximum Thermal Resistance JC (per leg) Package = TO-220AB, TO-262, & TO-263 Package = ITO-220	R⊕ _{JC}	2 4		°C/W
Operating and Storage Junction Temperature	TJ	-65 to +175		°C

 $^{^{\}star}$ Pulse width < 300 uS, Duty cycle < 2%



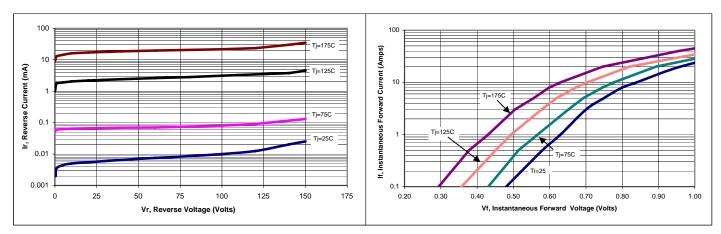


Figure 1: Typical Reverse Current

Figure 2: Typical Forward Voltage

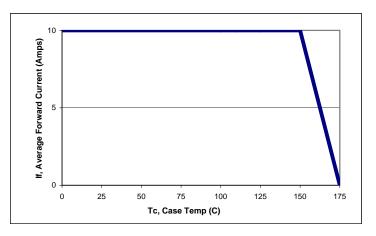


Figure 3: Current Derating, Case

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